

HE8812SG

GaAlAs Infrared Emitting Diodes

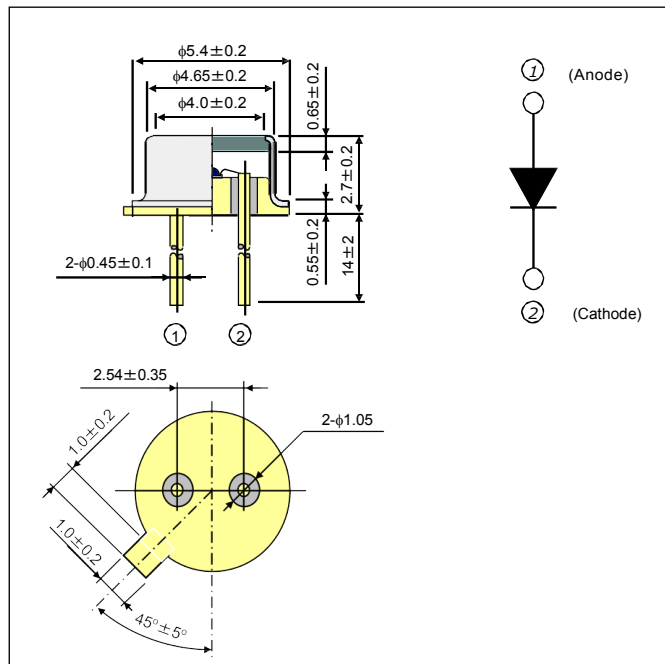
<Specifications>

- Peak Wavelength: 870nm typ.
- High Output, High Efficiency
- Narrow Spectral Width
- Wide Radiation Directivity
- High Reliability

<Application>

- Exposure Equipment
- Photoelectric Sensor
- Medical Equipment
- Metering Equipment

Outer Dimension (Unit:mm)



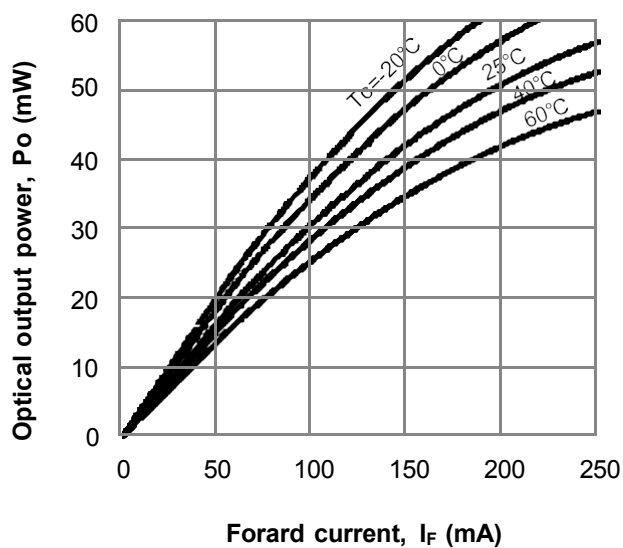
Absolute Maximum Ratings [Tc=25°C]			
Item	Symbol	Ratings	Unit
Forward Current	IF	250	mA
Reverse Voltage	VR	3	V
Operating Temperature	TOPR	-20 ~ +60	°C
Storage Temperature	TSTG	-40 ~ +90	°C

Electro-Optical Characteristics [Tc=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Optical Output Power	Pf*	IF=200mA	40	50		mW
Peak Wavelength	λp	IF=200mA	840	870	900	nm
Spectral Width	Δλ	IF=200mA		50	60	nm
Forward Voltage	VF	IF=200mA		1.8	2.5	V
Reverse Current	IR	VR=3V			100	μA
Capacitance	Ct	VR=0V, f=1MHz		30		pF
Rise Time	tr	IF=50mA		10		ns
Fall Time	tf	IF=50mA		10		ns

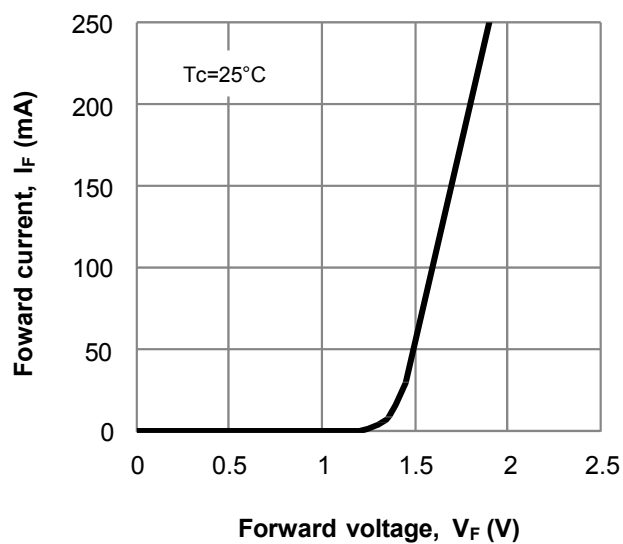


Typical Characteristic Curves

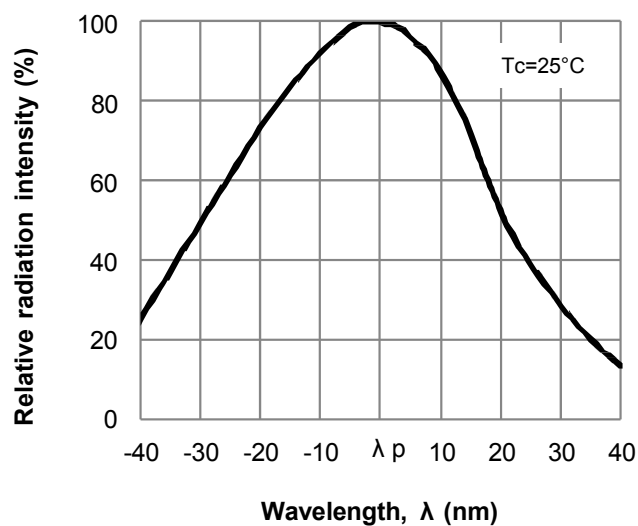
Optical Output Power vs. Forward Current



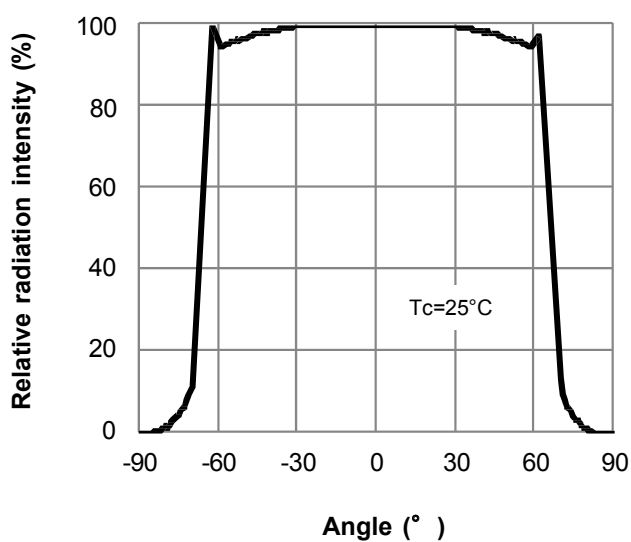
Forward Current vs. Forward Voltage



Wavelength Distribution



Radiation Directional



Disclaimer

Product specifications and data shown in this product catalog are subject to change without notice for the purposes of improving product performance, reliability, design, or otherwise.

Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

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